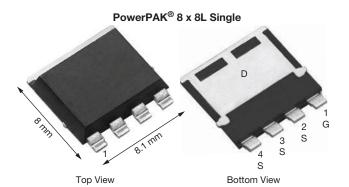
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**Vishay Siliconix** 

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET



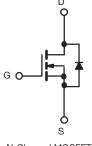
PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.00172
I <sub>D</sub> (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unless	otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain current	$T_{C}$ = 25 °C <sup>a</sup>	1	200		
Continuous drain current	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	124		
Continuous source current (diode conduction	n)	۱ <sub>S</sub>	136	A	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	600		
Single pulse avalanche current		I <sub>AS</sub>	85		
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	361	mJ	
Maximum power dissipation	power dissipation $T_{C} = 25 \text{ °C}$ PD 150		150	W	
T <sub>C</sub> = 125 °C		FD	50	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260	0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	1	0/10

Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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SQJQ404E

<b>SPECIFICATIONS</b> ( $T_C = 25$ °C	C, unless othe	erwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•			•			•
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	40	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3	3.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	: 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	100	-	-	Α
		$V_{GS} = 10 V$	I <sub>D</sub> = 20 A	-	0.00133	0.00172	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.00273	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.00330	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 20 A	-	160	-	S
Dynamic <sup>b</sup>	•			•			
Input capacitance	C <sub>iss</sub>			-	11 770	16 480	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	1255	1760	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	395	555	
Total gate charge <sup>c</sup>	Qg			-	175	270	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$ $V_{DS} = 20 V, I_D = 40 A$		-	46	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	27	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz	0.55	0.91	1.45	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	22	31	
Rise time <sup>c</sup>	tr	V <sub>DD</sub> =	= 20 V, R <sub>L</sub> = 0.5 Ω	-	23	33	ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 40 \text{ A},$	$V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$	-	58	81	
Fall time <sup>c</sup>	t <sub>f</sub>			-	8	21	
Source-Drain Diode Ratings and Ch	aracteristics <sup>b</sup>						
Reverse recovery time	t <sub>rr</sub>	V <sub>DD</sub> = 32 V, I <sub>FM</sub> = 40 A, di/dt = 100 A/µs		-	75	-	ns
Reverse recovery charge	Q <sub>rr</sub>			-	0.16	-	nC
Reverse recovery current	I <sub>RM</sub>		ναι – 100 Ανμο	-	-	-4.6	Α
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	450	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub>	= 50 A, V <sub>GS</sub> = 0	-	0.82	1.2	V

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

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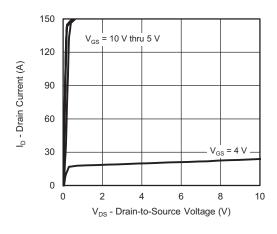
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

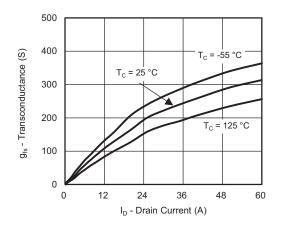


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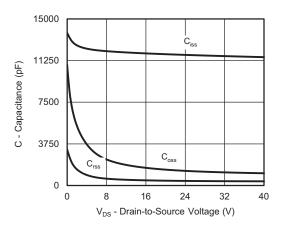
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



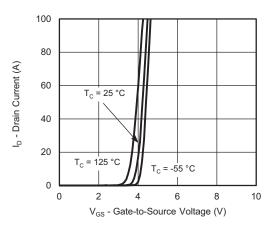
**Output Characteristics** 



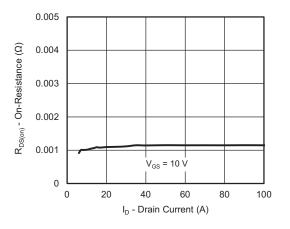
Transconductance



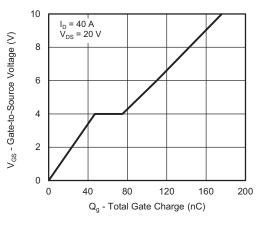
Capacitance



**Transfer Characteristics** 



**On-Resistance vs. Drain Current** 



Gate Charge

S18-0260-Rev. A, 05-Mar-18

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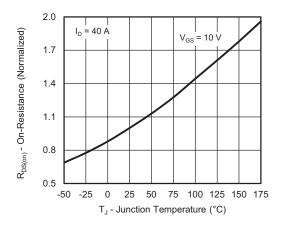
Document Number: 76570

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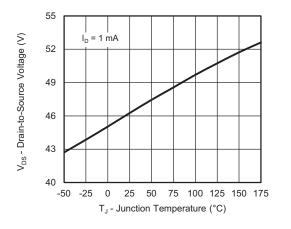


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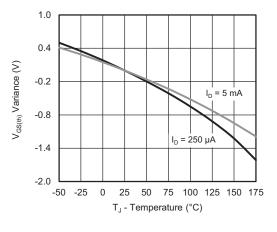
### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



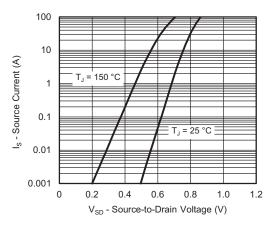
**On-Resistance vs. Junction Temperature** 



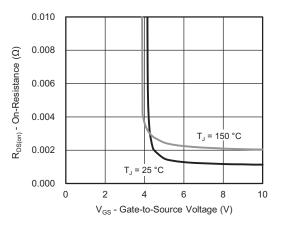
Drain Source Breakdown vs. Junction Temperature



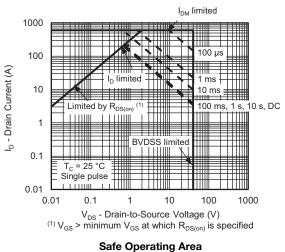
**Threshold Voltage** 



Source Drain Diode Forward Voltage



**On-Resistance vs. Gate-to-Source Voltage** 



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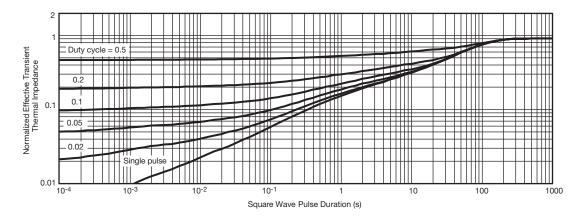
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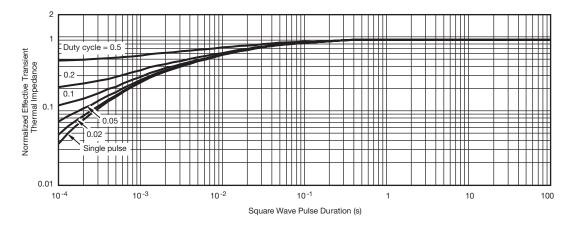


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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



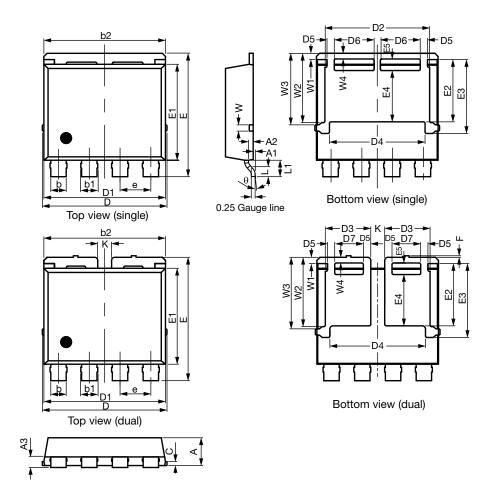
Normalized Thermal Transient Impedance, Junction-to-Case

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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

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# **Package Information**





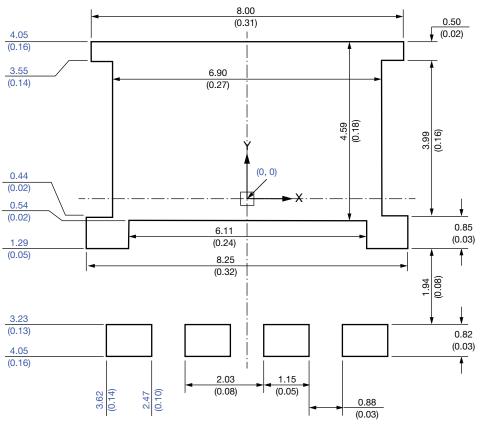
### Vishay Siliconix

DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



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# **Recommended Minimum PADs for PowerPAK® 8 x 8L Single**



Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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